

Atomic Force Microscopy Assisted Graphene 3D-Modification

Dmytro Nikolaievskiy^{1,2}, Cédric Pardanaud,² Céline Martin,² Pascale Roubin,² Alexandre Merlen,³ Sylvain Clair,³ Olivier Chuzel,¹ Jean-Luc Parrain¹

¹Aix Marseille Univ, CNRS, Centrale Marseille, iSm2, Marseille, France

²Aix Marseille Univ, CNRS, PIIM, Marseille, France

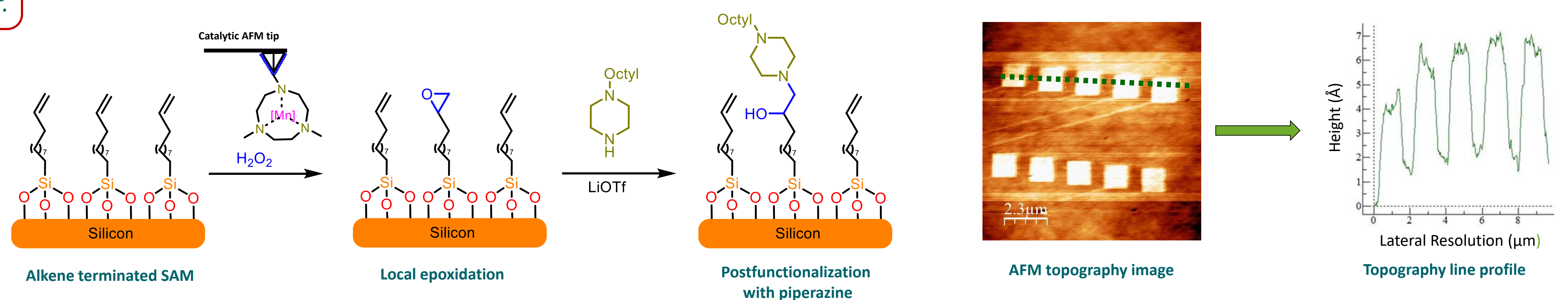
³Aix Marseille Univ, Toulon Univ, CNRS, IM2NP, Marseille, France

Methodology background.

Catalytic Scanning Probe Lithography (cSPL) validated on SAMs

Objective: to perform cSPL assisted epoxidation on a supported graphene layer.

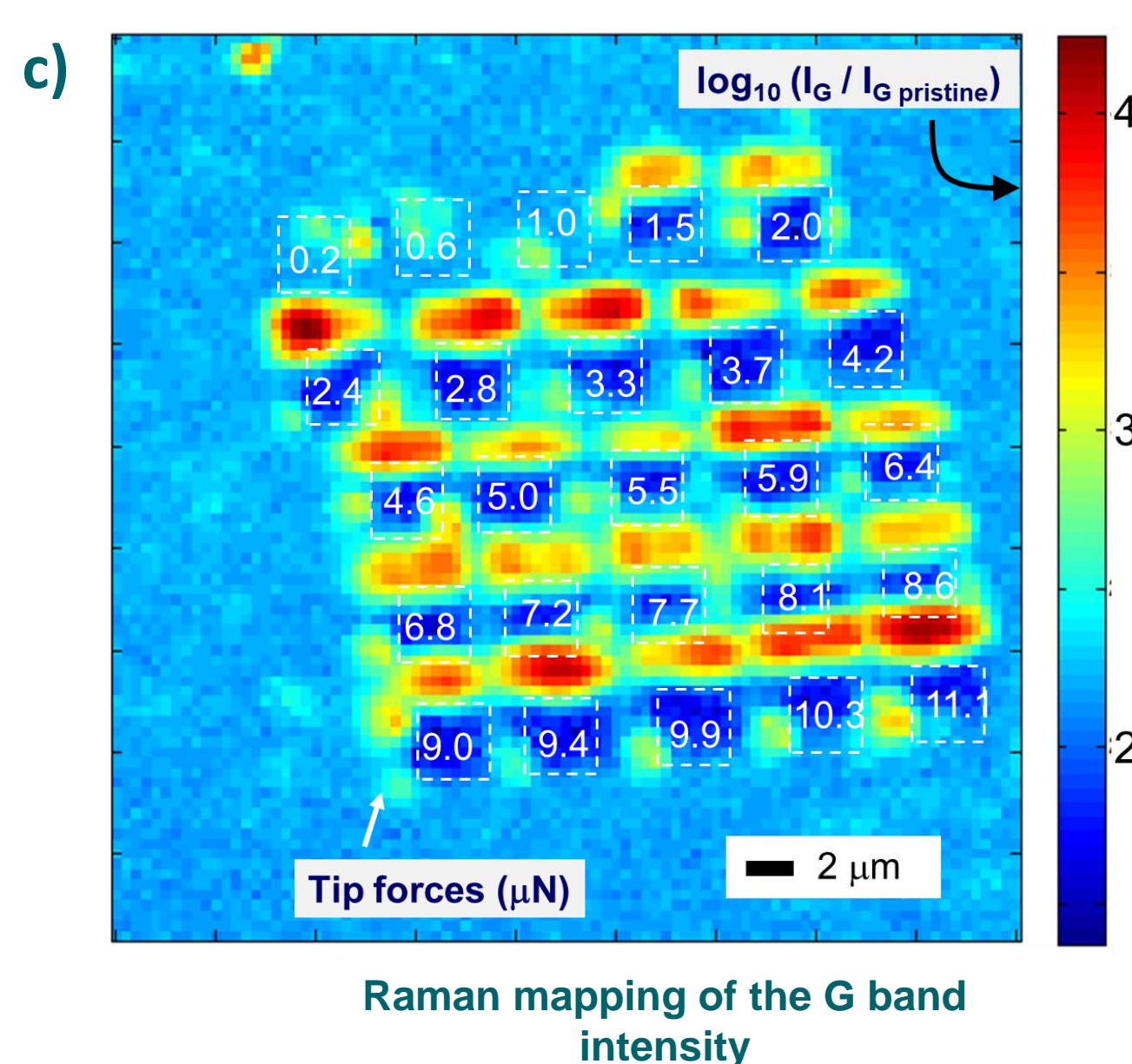
- ❖ Organometallic catalyst grafted on a silicon AFM tip.
- ❖ AFM tip provides a local catalytic chemical reaction.
- ❖ Epoxidation reaction optimized on alkene-terminated self-assembled monolayers (SAMs).
- ❖ Spatial resolution up to 40 nm. [1-3]



AFM tip assisted graphene folding

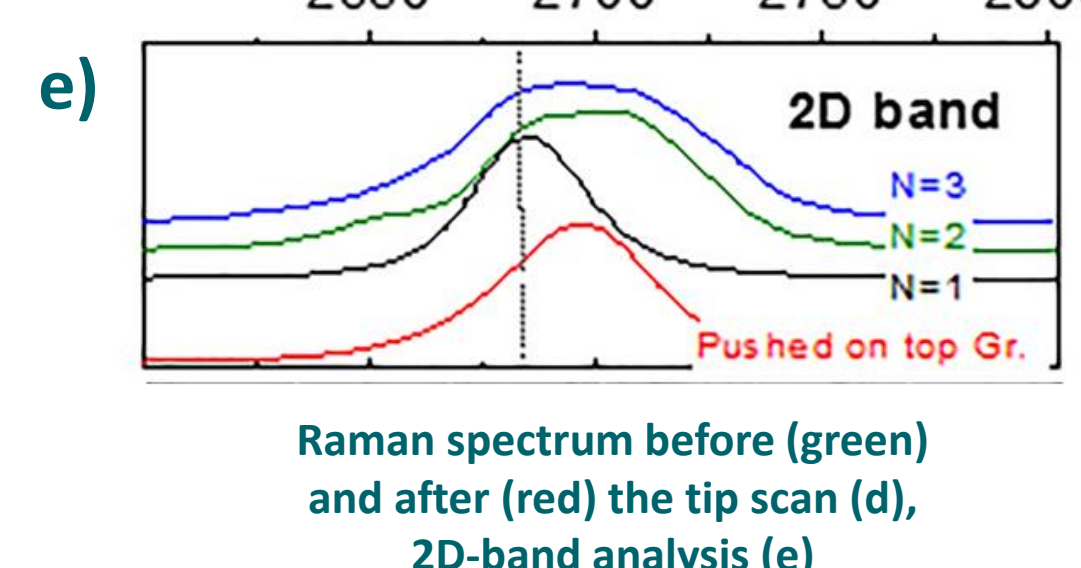
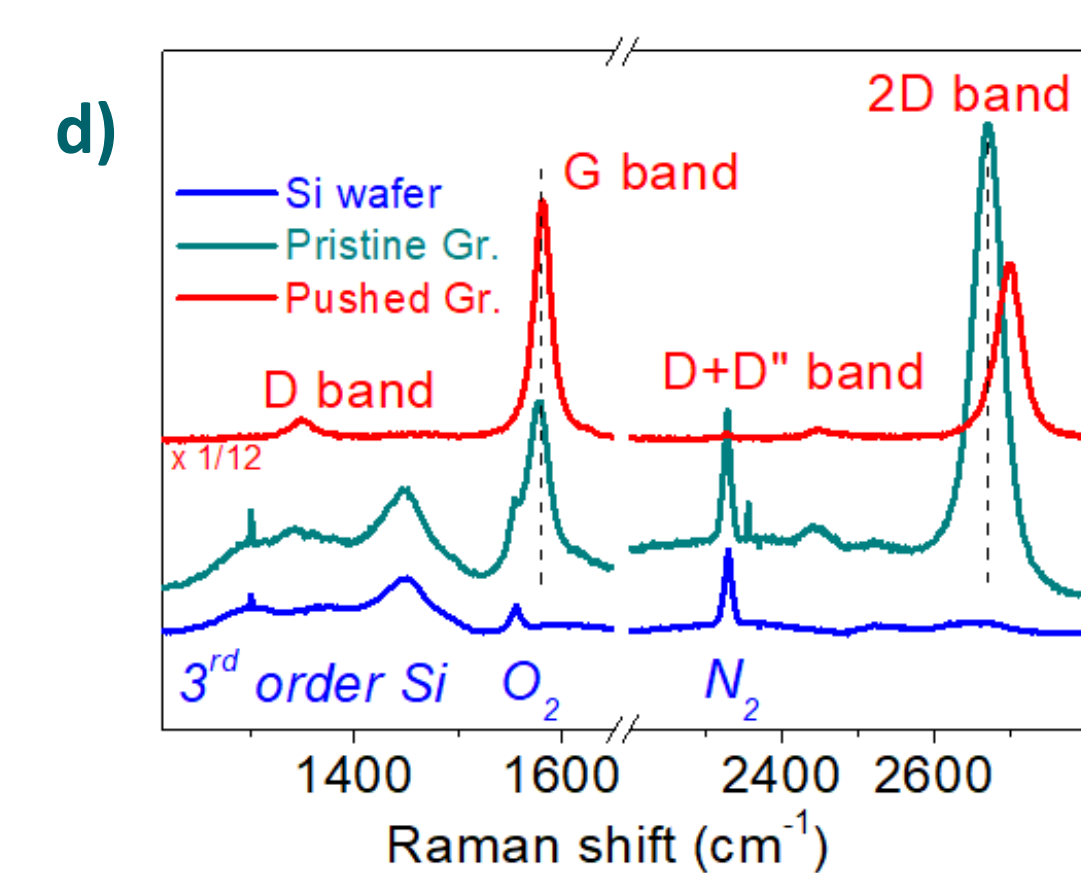
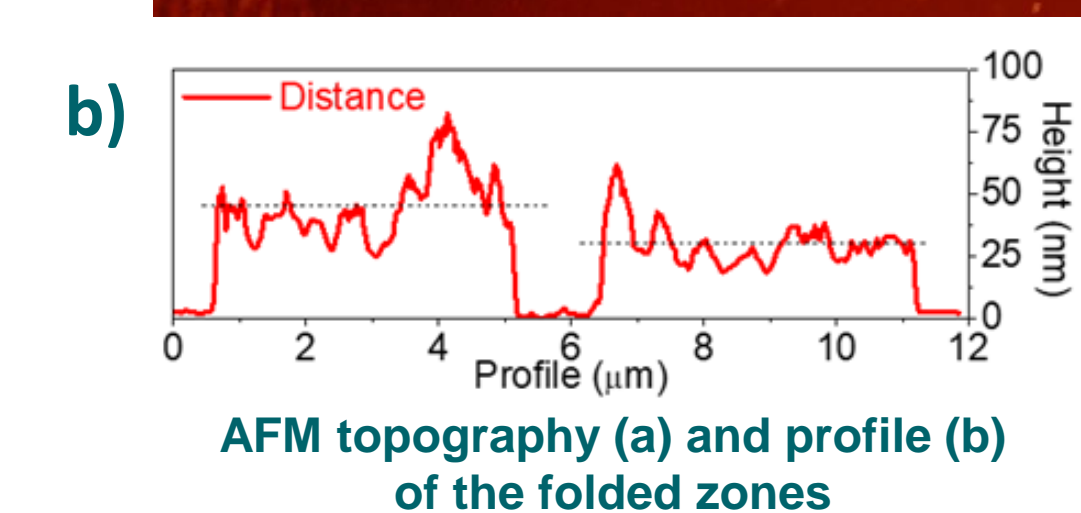
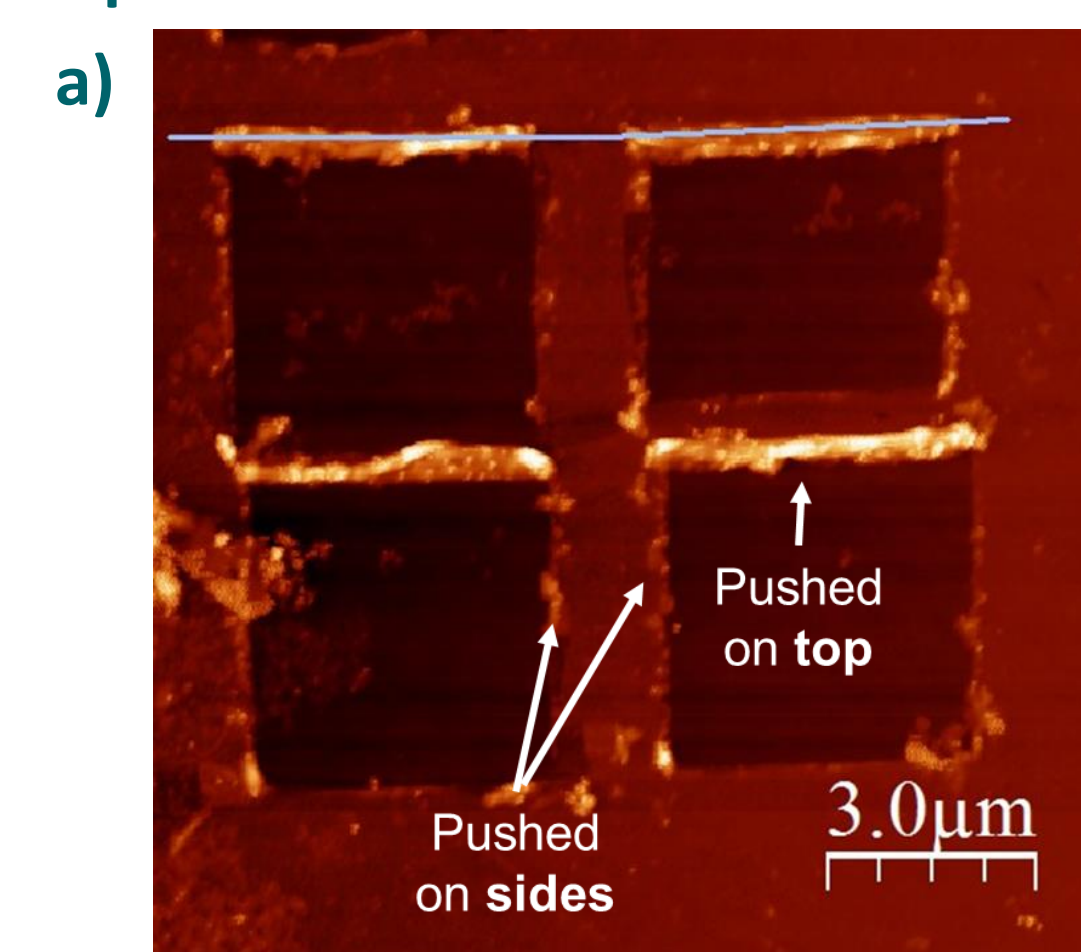
Experiments with catalytic Si AFM tip

During the optimization of tip force in reaction conditions (H_2O_2 , acetonitrile, catalytic AFM tip), the graphene in a series of treated square zones was **cut and pushed** on top and on sides (a,b).^[4]



Raman analysis of pushed graphene (c-e):

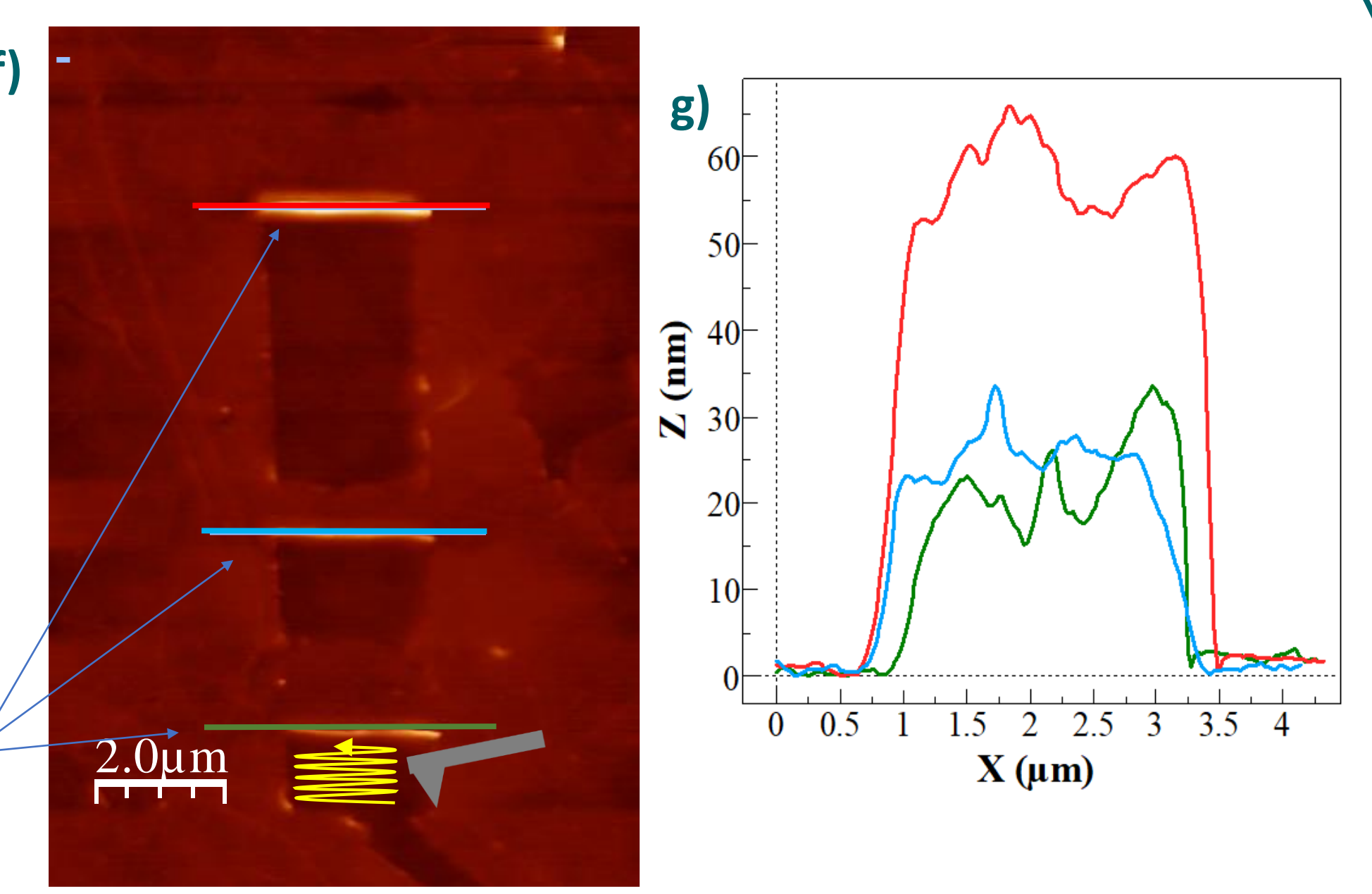
- G- and 2D-bands remain principal.
- G-band 100-fold intensification (c).
- Small D-band – limited defects introduced.
- 2D-band (e): neither bi-, tri-, quadrilayer graphene nor graphite, but SLG with a single or a bimodal Lorentzian shape;
- stacking misorientation and weaker Raman interaction between planes.



Experiments with non-catalytic Si AFM tip

Study of AFM tip induced graphene folding:

- non-catalytic AFM tip;
- atmospheric conditions (no reaction solution);
- series of **rectangular zones** treated with AFM tip **zig-zag movements** (f): 2x1, 2x2, 2x4 μm ;
- AFM measured **profiles** of folded structures from 20 to 60 nm (g).

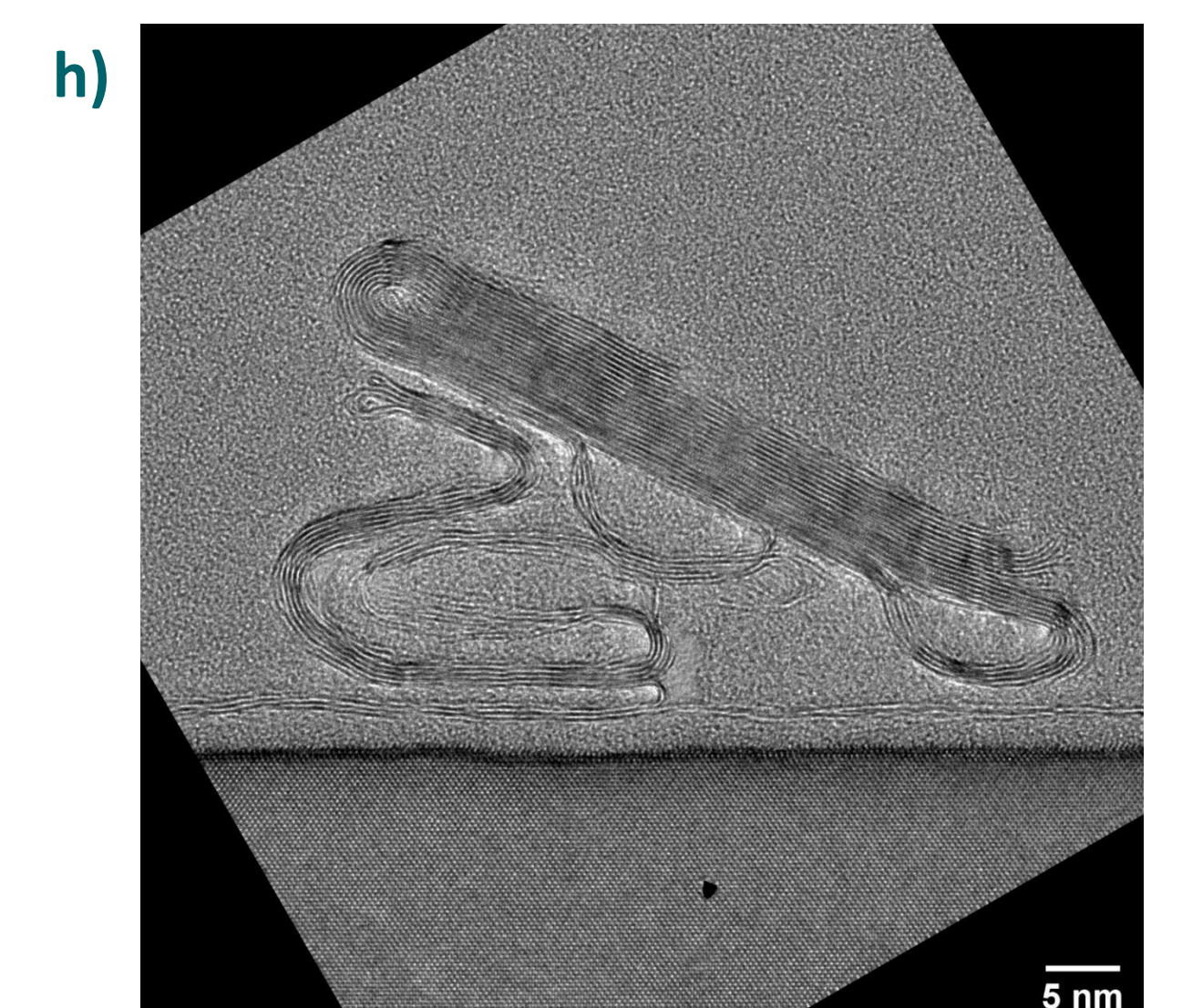


Technical and operational details:

- AFM tip: ACT «AppNano», Silicon.
- Graphene sample: CVD «Graphenea «Easy transfer», Si substrate «Siltronix», 500 μm thick.
- Lithography: contact mode, 512 lines per 4 μm , 1 line/s, tip force 6 μN .
- Topography: «tapping» mode, 0,2 line/s.

TEM analysis:

- A transverse cross-section of the folded structure prepared by FIB method.
- TEM analysis revealed enrolled and well-stacked graphene layers (h).
- Average Interlayer distance 0,33 nm (close to graphite).



TEM image of the cross-section of the folded structure

Conclusions and Perspectives

- ❖ A versatile cSPL technique for high-resolution SAM functionalization was developed.
- ❖ cSPL essays on supported graphene layers lead to the graphene folding and stacking.
- ❖ Raman and TEM analysis of the folded structures revealed well-stacked misoriented multilayer formations, further characterizations are envisaged.
- ❖ Spatially resolved covalent cSPL graphene functionalization experiments are on-going.

CONTACT PERSON

Dmytro Nikolaievskiy
dmytro.nikolaievskiy
@univ-amu.fr

REFERENCES

- [1] D. A. Valyaev, S. Clair, L. Patrone *et al*, *Chem. Sci.*, 2013, 4, 2815.
- [2] V. Mesquita, J. Botton, D. A. Valyaev, *et al*, *Langmuir*, 2016, 32, 4034.
- [3] J. Botton, K. Gratzner, C. François, *et al.*, *Chem. Sci.* 2018, 9, 4280.
- [4] C. Pardanaud, A. Merlen, K. Gratzner, *et al.*, *J. Phys. Chem. Lett.* 2019, 10, 3571.